NSN 5961-01-356-1382

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-356-1382 **Inclosure Material:** Glass **Overall Length:** Between 0.010 inches and 0.012 inches **Overall Height:** Between 0.001 inches and 0.002 inches Overall Width: Between 0.006 inches and 0.010 inches **Function For Which Designed:** Detector **End Application:** B-2 (atb) bomber aircraft. **Mounting Method:** Press fit **Features Provided:** Electrostatic sensitive and hermetically sealed case **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 4.0 breakdown voltage, dc **Power Rating Per Characteristic:** 150.0 milliwatts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Special Features:** Hardness critical process; junction pattern arrangement: pn **Precious Material And Location:** Terminals gold **Precious Material: Terminal Type And Quantity:** 2 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli

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